| -(| 5 | • • | | |
|----|---|---------|------------|----|
| | | SEMIKRO | SKT 1000/1 | ZT |
| | | | | |

Capsule Thyristor

| Line | Thyristor |
|------|-----------|
|------|-----------|

SKT 1000

Features

- Hermetic metal case with ceramic insulator
- Capsule package for double sided cooling
- International standard case
- Off-state and reverse voltages up to 2800 V
- Amplifying gate

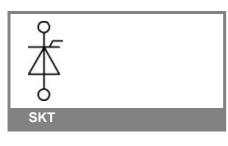
Typical Applications

- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers (e. g. for temperature control)
- Recommended snubber network

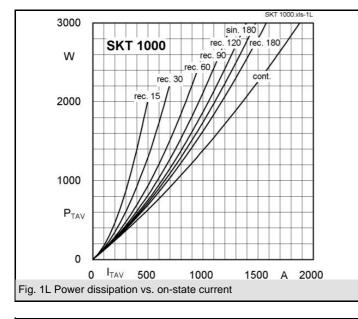
e. g. for V_{VRMS}
$$\leq$$
 400 V:
R = 33 Ω/32 W, C = 1 µF

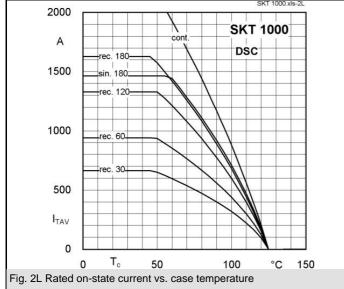
| V _{RSM} | V _{RRM} , V _{DRM} | I _{TRMS} = 2300 A (maximum value for continuous operation) | | |
|------------------|-------------------------------------|---|--|--|
| V | V | I _{TAV} = 1000 A (sin. 180; DSC; T _c = 85 °C) | | |
| 1300 | 1200 | SKT 1000/12E | | |
| 1700 | 1600 | SKT 1000/16E | | |
| 2300 | 2200 | SKT 1000/22EL2 | | |
| 2700 | 2600 | SKT 1000/26EL2 | | |
| 2900 | 2800 | SKT 1000/28EL2 | | |

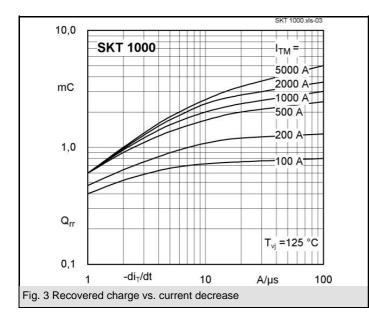
| Symbol | Conditions | Values | Units |
|-----------------------------------|---|----------------|-------|
| I _{TAV} | sin. 180; T _c = 100 (85) °C | 710 (1000) | А |
| I _D | 2 x P8/180; T _a = 45 °C; B2 / B6 | 360 / 500 | А |
| | 2 x P8/180F; T _a = 35 °C; B2 / B6 | 1250 /1750 | А |
| I _{RMS} | 2 x P8/180; T _a = 45 °C; W1C | 400 | А |
| I _{TSM} | T _{vi} = 25 °C; 10 ms | 19000 | Α |
| | T _{vi} = 125 °C; 10 ms | 16500 | А |
| i²t | T _{vj} = 25 °C; 8,3 10 ms | 1800000 | A²s |
| | T _{vj} = 125 °C; 8,3 10 ms | 1360000 | A²s |
| V _T | T _{vi} = 25 °C; I _T = 3600 A | max. 2 | V |
| V _{T(TO)} | T _{vi} = 125 °C | max. 1,14 | V |
| r _T | T _{vj} = 125 °C | max. 0,243 | mΩ |
| I _{DD} ; I _{RD} | T_{vj} = 125 °C; V_{RD} = V_{RRM} ; V_{DD} = V_{DRM} | max. 100 | mA |
| t _{gd} | T _{vj} = 25 °C; I _G = 1 A; di _G /dt = 1 A/μs | 1 | μs |
| t _{gr} | $V_{\rm D} = 0.67 * V_{\rm DRM}$ | 2 | μs |
| (di/dt) _{cr} | T _{vi} = 125 °C | max. 125 | A/µs |
| (dv/dt) _{cr} | T _{vi} = 125 °C | max. 1000 | V/µs |
| t _q | T _{vi} = 125 °C | 100 250 | μs |
| I _H | T _{vj} = 25 °C; typ. / max. | 250 / 500 | mA |
| I _L | T _{vj} = 25 °C; R _G = 33 Ω; typ. / max. | 500 / 2000 | mA |
| V _{GT} | T _{vi} = 25 °C; d.c. | min. 5 | V |
| I _{GT} | T _{vj} = 25 °C; d.c. | min. 250 | mA |
| V _{GD} | $T_{vj} = 125 \text{ °C; d.c.}$ | max. 0,25 | V |
| I _{GD} | T _{vj} = 125 °C; d.c. | max. 10 | mA |
| R _{th(j-c)} | cont.; DSC | 0,021 | K/W |
| R _{th(j-c)} | sin. 180; DSC / SSC | 0,0225 / 0,054 | K/W |
| R _{th(j-c)} | rec. 120; DSC / SSC | 0,027 / 0,06 | K/W |
| R _{th(c-s)} | DSC / SSC | 0,005 / 0,01 | K/W |
| T _{vj} | | - 40 + 125 | °C |
| T _{stg} | | - 40 + 130 | °C |
| V _{isol} | | - | V~ |
| F | mounting force | 22 25 | kN |
| а | | | m/s² |
| m | approx. | 480 | g |
| Case | | B 14 | |
| | | | |
| | | | |

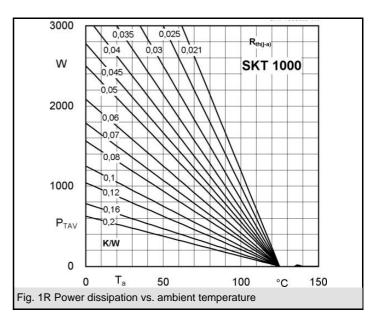


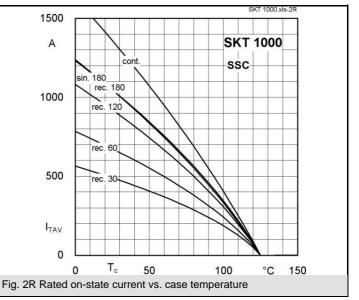
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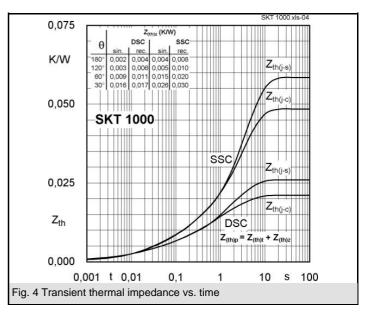




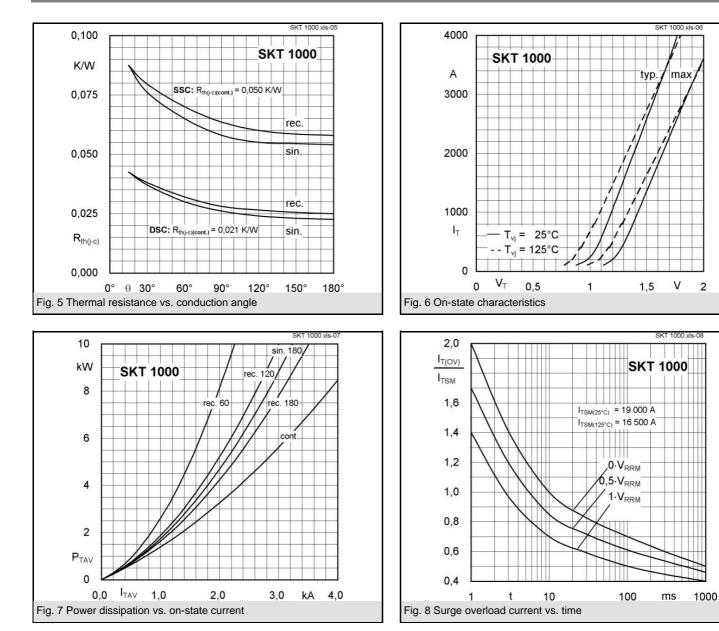


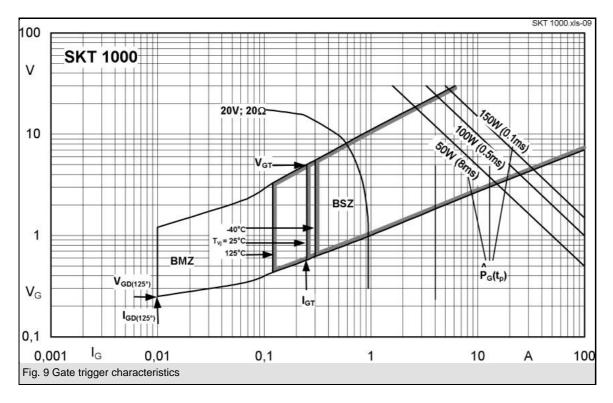


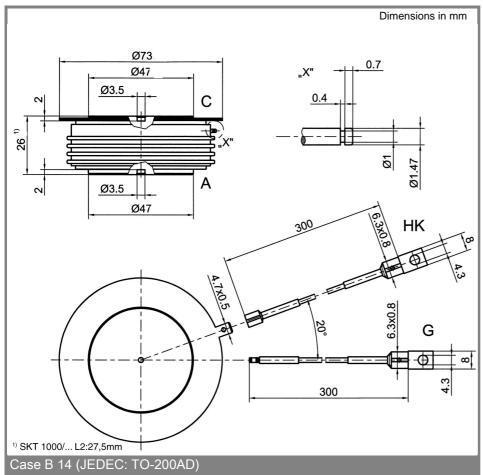




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